

Common Anode Quad Array Switching Diode

NSDEMP11XV6T1, NSDEMP11XV6T5

These Common Anode Epitaxial Planar QUAD Diodes are designed for use in ultra high speed switching applications. The NSDEMP11XV6T1 device is housed in the SOT-563 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Fast t_{rr}
- Low C_D
- These are Pb-Free Devices

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Reverse Voltage	V_{R}	80	Vdc
Peak Reverse Voltage	V_{RM}	80	Vdc
Forward Current	IF	100	mAdc
Peak Forward Current	I _{FM}	300	mAdc
Peak Forward Surge Current	I _{FSM} (Note 1)	2.0	Adc

THERMAL CHARACTERISTICS

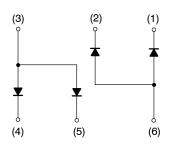
Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P _D	357 (Note 2) 2.9 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	350 (Note 2)	°C/W
Characteristic			_
(Both Junctions Heated)	Symbol	Max	Unit
(Both Junctions Heated) Total Device Dissipation T _A = 25°C Derate above 25°C	Symbol P _D	500 (Note 2) 4.0 (Note 2)	mW mW/°C
Total Device Dissipation T _A = 25°C	,	500 (Note 2) 4.0	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

1. $t = 1 \mu S$

2. FR-4 @ Minimum Pad





SOT-563 CASE 463A PLASTIC

MARKING DIAGRAM



P9 = Device Code M = Date Code • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NSDEMP11XV6T1	SOT-563*	4000/Tape & Reel
NSDEMP11XV6T1G	SOT-563*	4000/Tape & Reel
NSDEMP11XV6T5	SOT-563*	8000/Tape & Reel
NSDEMP11XV6T5G	SOT-563*	8000/Tape & Reel

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- *This package is inherently Pb-Free.

NSDEMP11XV6T1, NSDEMP11XV6T5

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I _R	V _R = 70 V	_	0.1	μAdc
Forward Voltage	V _F	I _F = 100 mA	-	1.2	Vdc
Reverse Breakdown Voltage	V_{R}	I _R = 100 μA	0	-	Vdc
Diode Capacitance	C _D	V _R = 6.0 V, f = 1.0 MHz	-	3.5	pF
Reverse Recovery Time	t _{rr} (Note 3)	I_F = 5.0 mA, V_R = 6.0 V, R_L = 100 Ω , I_{rr} = 0.1 I_R	-	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. t_{rr} Test Circuit for NSDEMP11XV6T1 in Figure 4.

TYPICAL ELECTRICAL CHARACTERISTICS

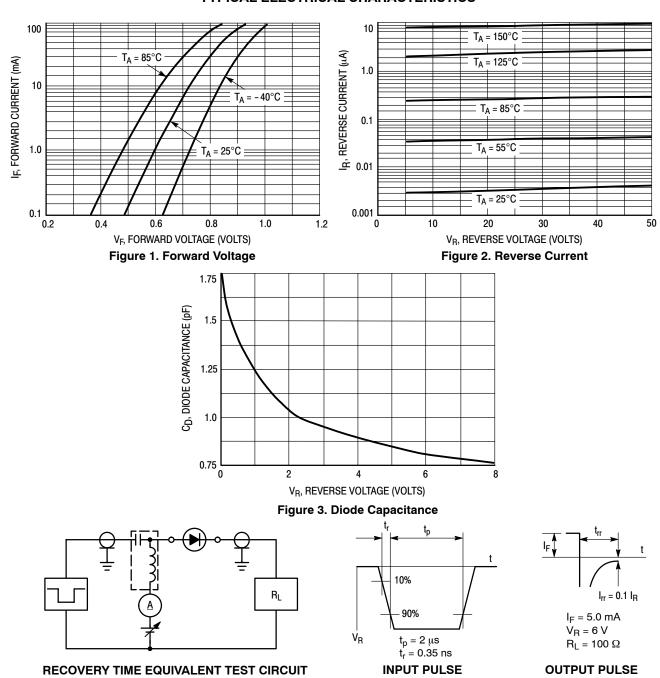


Figure 4. Reverse Recovery Time Test Circuit for the NSDEMP11XV6T1



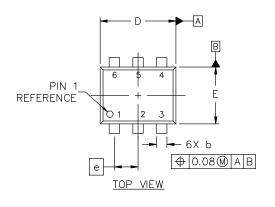


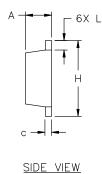
SOT-563-6 1.60x1.20x0.55, 0.50P CASE 463A **ISSUE J**

DATE 15 FEB 2024

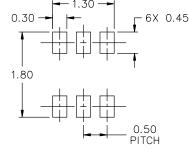
NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.





DIM	M:	ILLIMETE	RS
INITU	MIN.	N□M.	MAX.
Α	0.50	0.55	0.60
b	0.17	0.22	0.27
\cup	0.08	0.13	0.18
D	1.50	1.60	1.70
Ε	1.10	1.20	1.30
е	0.50 BSC		
I	1.50	1.60	1.70
L	0.10	0.20	0.30
D E e	1.50 1.10 1.50	1.60 1.20 0.50 BSC	1.70 1.30



STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHODE 1
2. BASE 1	2. EMITTER 2	2. CATHODE 1
3. COLLECTOR 2	3. BASE 2	3. ANDDE/ANDDE 2
4. EMITTER 2	4. COLLECTOR 2	4. CATHODE 2
5. BASE 2	5. BASE 1	5. CATHODE 2
6. COLLECTOR 1	6. COLLECTOR 1	6. AN□DE/AN□DE 1

STYLE 6: PIN 1. CATHODE 2. ANODE

3. CATHODE 4. CATHODE 5. CATHODE

RECOMMENDED	MOLINITING	FOOTPRINT*
KECOMIMENDED	MOONTING	LOO INKINI.

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 7: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE	STYLE 8: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SDURCE 5. DRAIN	STYLE 9: PIN 1. SUURCE 1 2. GATE 1 3. DRAIN 2 4. SUURCE 2 5. GATE 2
6. CATH□DE	6. DRAIN	6. DRAIN 1

STYLE 5:

PIN 1. CATHODE

2. CATHODE

3. ANDDE 4. ANDDE 5. CATHODE

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Month Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 10:	STYLE 11:
PIN 1. CATHODE 1	PIN 1. EMITTER 2
2. N/C	2. BASE 2
3. CATHODE 2	3. COLLECTOR 1
4. ANDDE 2	4. EMITTER 1
5. N/C	5. BASE 1
C ANDDE 1	4 COLLECTOR 2

STYLE 4: PIN 1. COLLECTOR

2. COLLECTOR

3. BASE 4. EMITTER 5. COLLECTOR

COLLECTOR

DOCUMENT NUMBER:

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98AON11126D **DESCRIPTION:** SOT-563-6 1.60x1.20x0.55, 0.50P

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